

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"US 20090108247"	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/05/14 09:08
S2	2	"5883827".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:34
S3	2	"5,414,271".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:38
S4	112	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:43
S5	86	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8"))))) and (phase with change)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:43

S6	48	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))) and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:44
S7	40	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))) and electrode and (storage or memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:44
S8	9	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))) and (electrode with transp\$6) and (storage or memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:50
S9	4	"3,271,591".did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:56
S10	112	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8"))))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 10:57

S11	16	(reversible with phase with change) and (ge near te) with (volume or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 11:10
S12	13	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))) and (electrode with transp\$6) and (zn or zinc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 12:42
S13	12	(chalcogenide or (phase with change with material)) and ((chalcogenide or material) with ((ge or germanium) and (te or tellurium) and (group with (2B or 1B or 3A or 7A or "8")))) and (electrode with transparent) and (zn or zinc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 12:46
S14	1	(10/790881).APP.	USPAT; USOCR	WITH	ON	2009/05/14 13:00
S15	1162	(phase with change with material) and (transparent with electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 13:36
S16	57	(phase with change with material) and (transparent with electrode) and (phase with change with memory with device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 13:37

S17	26	(phase with change with material) and (transparent with electrode) and (phase with change with crystal with amorphous)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 13:38
S18	138	(transmittance with phase with change with material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 17:09
S19	138	(transmittance with phase with change with material) and transmittance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 17:09
S20	118	(transmittance with phase with change with material) and (transmittance with light)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 17:11
S21	23	(word with lines with data) with phase with change with material	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:45
S22	131	(word with lines with data) with phase with change	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:45
S23	81	(word with lines with data) with phase with change and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:45
S24	1	(10/485566).APP.	USPAT; USOCR	WITH	ON	2009/05/14 18:47

S25	772	(word with lines with data) and (phase with change) and electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:48
S26	680	(word with lines with data) and (phase with change) and electrode and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:49
S27	600	(word with lines with data) and (phase with change) and electrode and semiconductor and memory with device	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/05/14 18:49

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